Abstracts

20 GHz Band GaAs-FET Waveguide-Type Amplifier

H. Tohyama. "20 GHz Band GaAs-FET Waveguide-Type Amplifier." 1977 MTT-S International Microwave Symposium Digest 77.1 (1977 [MWSYM]): 246-248.

Negative conductance reflection-type GaAs-FET amplifier was studied. Calculation showed a packaged GaAs-FET could be operated at high frequency than 20 GHz. An amplifier with 17 dB gain at 20 GHz was obtained using a packaged GaAs-FET mounted in waveguide circuit.

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